

BLF6G27L-50BN

Power LDMOS transistor

Rev. 3 — 8 October 2014

Product data sheet

1. Product profile

1.1 General description

50 W LDMOS power transistor for base station applications at frequencies from 2500 MHz to 2700 MHz.

Table 1. Typical performance

RF performance at $T_{case} = 25\text{ °C}$ in a common source class-AB production test circuit.

Test signal	f	I_{DQ}	V_{DS}	$P_{L(AV)}$	G_p	η_D	ACPR
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2500 to 2700	430	28	3	16.5	14.5	-47 [1]

[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF per carrier; carrier spacing 5 MHz

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (2500 MHz to 2700 MHz)
- Internally matched for ease of use
- Integrated current sense
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

1.3 Applications

- RF power amplifiers for base stations and multi carrier applications in the 2500 MHz to 2700 MHz frequency range



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain		
2	gate		
3	source [1]		
4, 5	sense drain		
6, 7	sense gate		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF6G27L-50BN	-	flanged ceramic package; 2 mounting holes; 6 leads	SOT1112A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
$V_{GS(sense)}$	sense gate-source voltage		-0.5	+9	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-case)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C}; P_L = 12.5\text{ W (CW)}$	1.3	K/W

6. Characteristics

Table 6. Characteristics

$T_j = 25\text{ °C}$ per section; unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}$; $I_D = 0.5\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 72\text{ mA}$	1.4	1.9	2.4	V
I_{Dq}	quiescent drain current	sense transistor: $I_{DS} = 9.1\text{ mA}$; $V_{DS} = 26.5\text{ V}$ main transistor: $V_{DS} = 28\text{ V}$	380	430	480	mA
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}$; $V_{DS} = 28\text{ V}$	-	-	1.5	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $V_{DS} = 10\text{ V}$	10	12	-	A
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	150	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}$; $I_D = 3.6\text{ A}$	-	5.0	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $I_D = 2.52\text{ A}$	-	0.25	-	Ω

7. Application information

Table 7. 2-carrier W-CDMA application information

All testing performed in Class-AB production test circuit; test signal 3GPP; test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF per carrier; carrier spacing 5 MHz; $f_1 = 2500\text{ MHz}$; $f_2 = 2600\text{ MHz}$; $f_3 = 2700\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}$; $I_{Dq} = 430\text{ mA}$; $T_{case} = 25\text{ °C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)} = 3\text{ W}$	15.3	16.5	-	dB
η_D	drain efficiency	$P_{L(AV)} = 3\text{ W}$	12.5	14.5	-	%
ACPR	adjacent channel power ratio	$P_{L(AV)} = 3\text{ W}$	-	-47	-43	dBc
I_{Dq}	quiescent drain current	$V_{DD} = 28\text{ V}$	-	430	-	mA

Table 8. 1-carrier W-CDMA application information

All testing performed in Class-AB production test circuit; test signal 3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF per carrier; $f = 2700\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}$; $I_{Dq} = 430\text{ mA}$; $T_{case} = 25\text{ °C}$; unless otherwise specified.

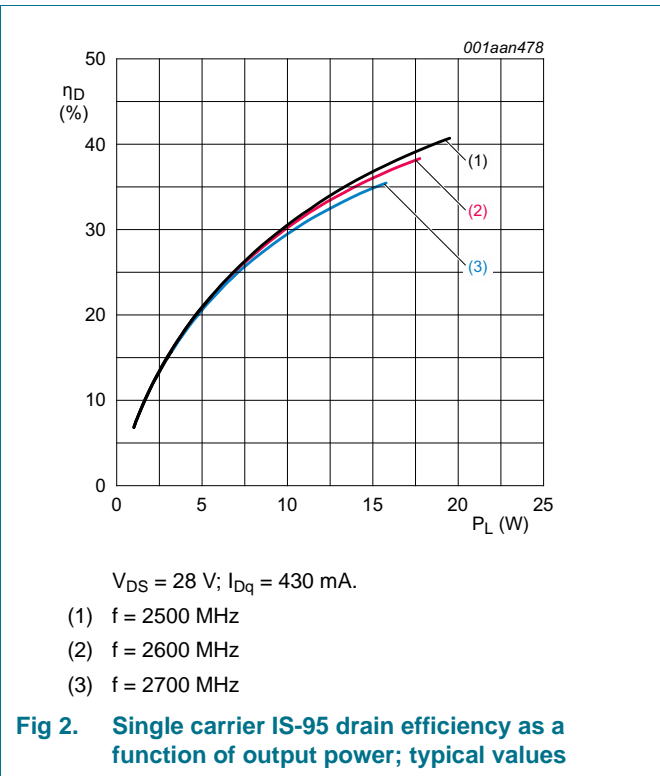
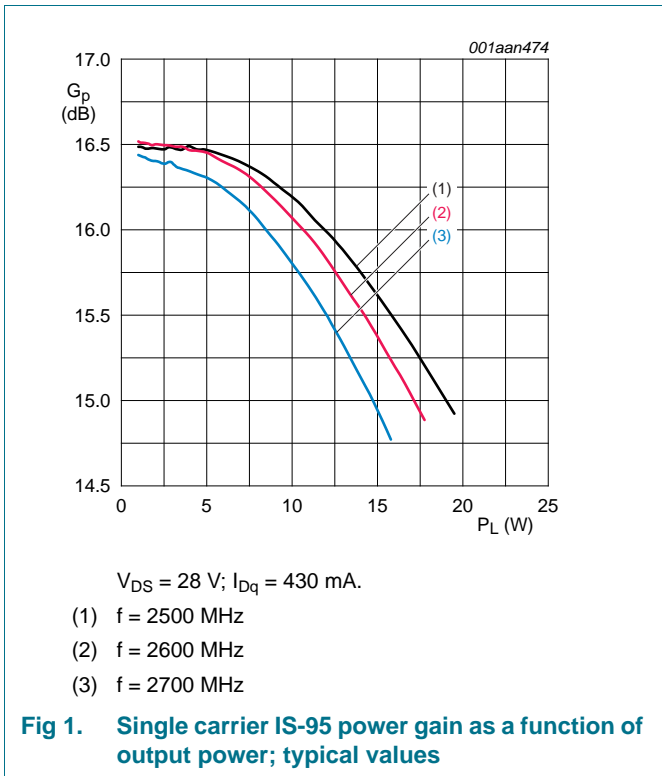
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PAR_O	output peak-to-average ratio	$P_{L(AV)} = 16\text{ W}$	4.1	4.7	5.3	dB

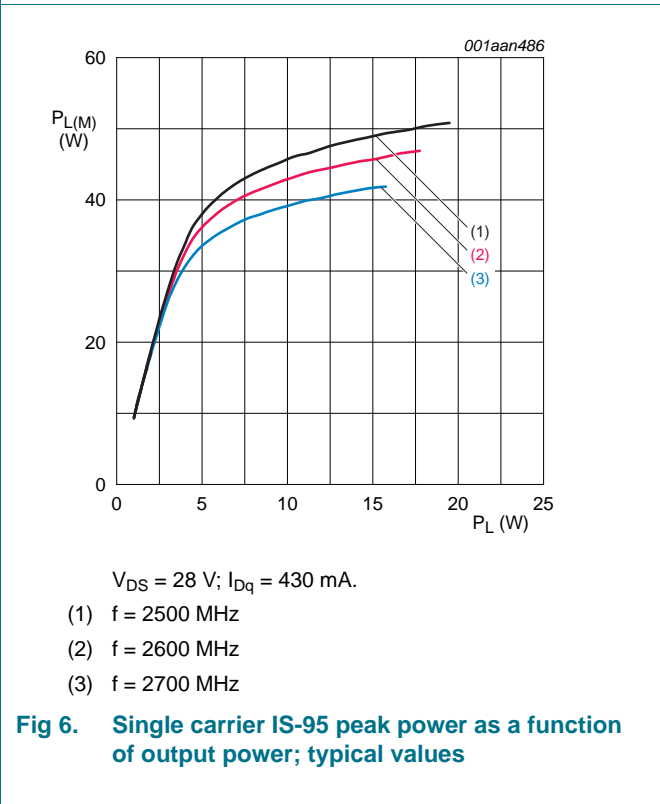
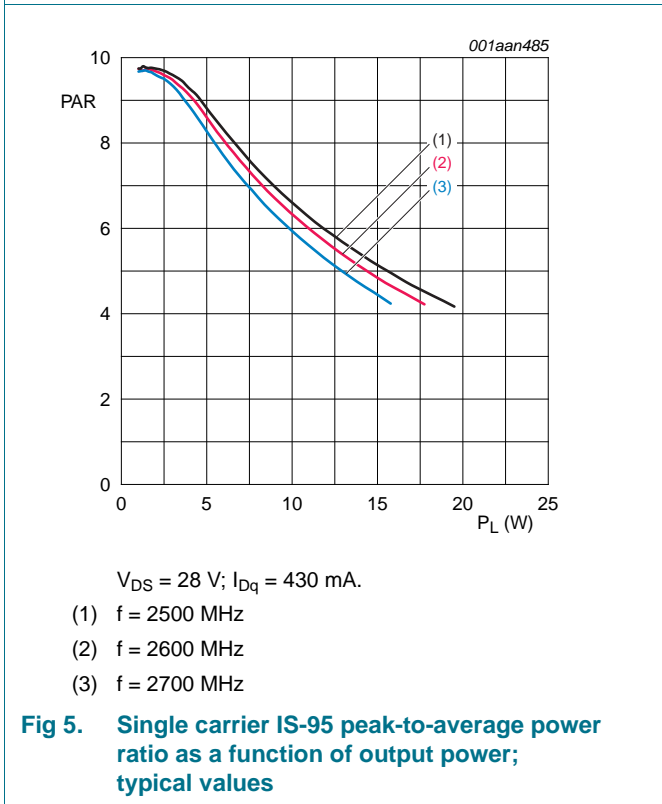
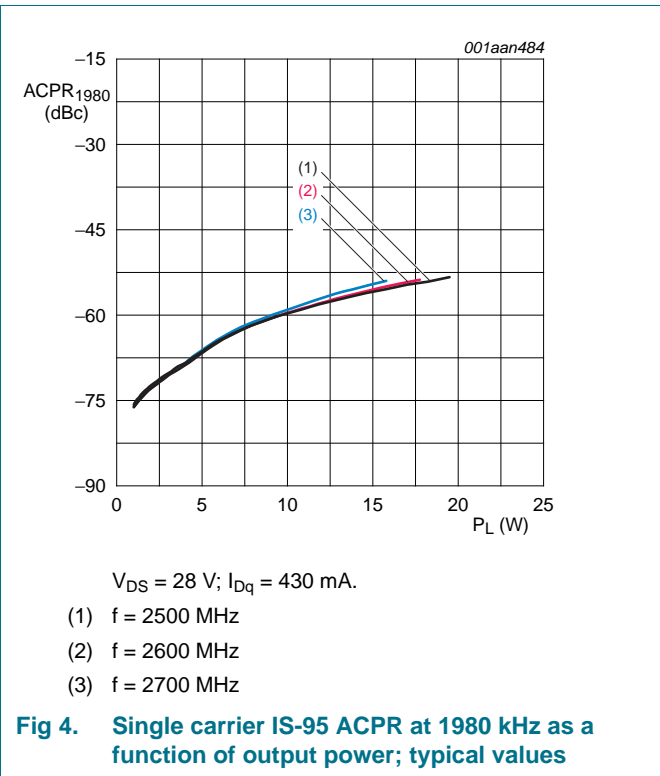
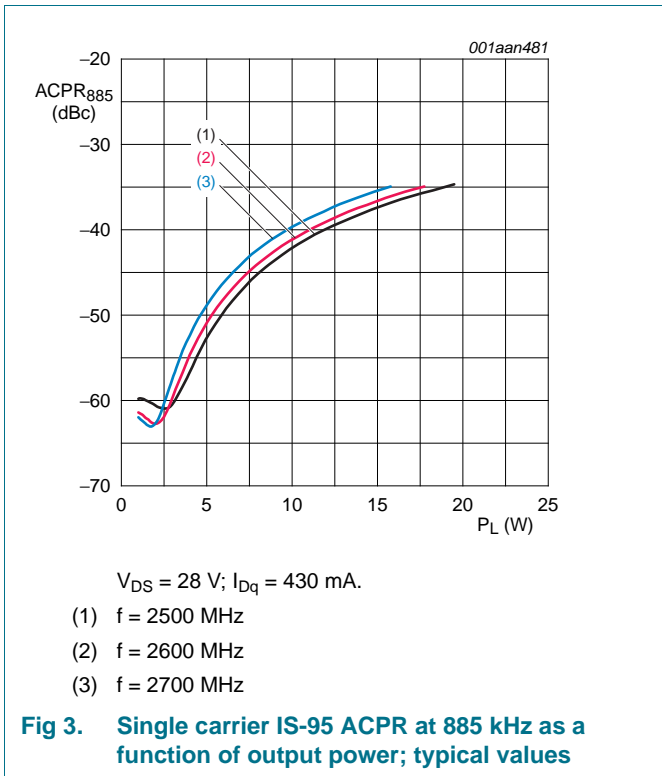
7.1 Ruggedness in Class-AB operation

The BLF6G27L-50BN is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28\text{ V}$; $I_{Dq} = 430\text{ mA}$; $P_L = 40\text{ W}$ (CW); $f = 2500\text{ MHz}$.

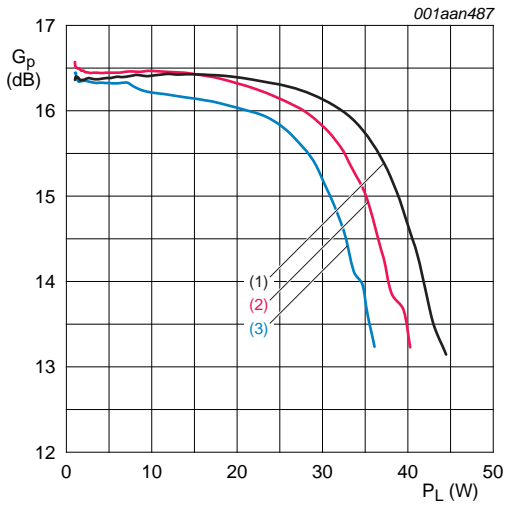
7.2 Single carrier IS-95

Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13).
 PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.



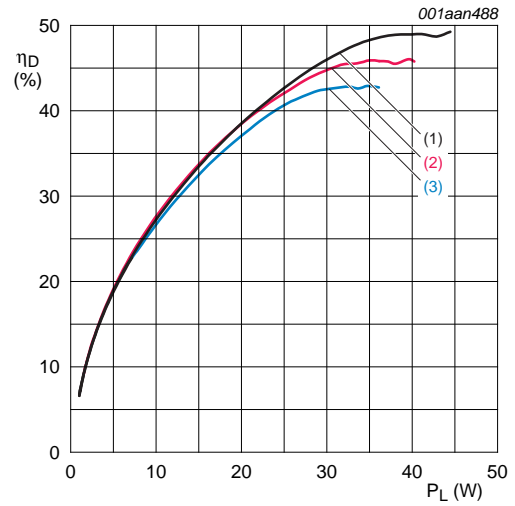


7.3 Pulsed CW



$V_{DS} = 28\text{ V}; I_{Dq} = 430\text{ mA}.$
 (1) $f = 2500\text{ MHz}$
 (2) $f = 2600\text{ MHz}$
 (3) $f = 2700\text{ MHz}$

Fig 7. Pulsed CW power gain as a function of output power; typical values

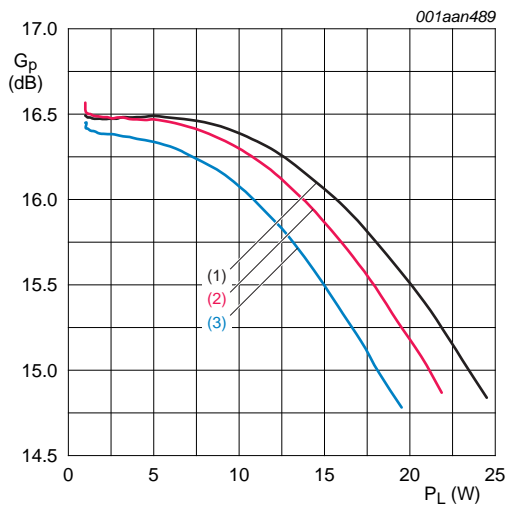


$V_{DS} = 28\text{ V}; I_{Dq} = 430\text{ mA}.$
 (1) $f = 2500\text{ MHz}$
 (2) $f = 2600\text{ MHz}$
 (3) $f = 2700\text{ MHz}$

Fig 8. Pulsed CW drain efficiency as a function of output power; typical values

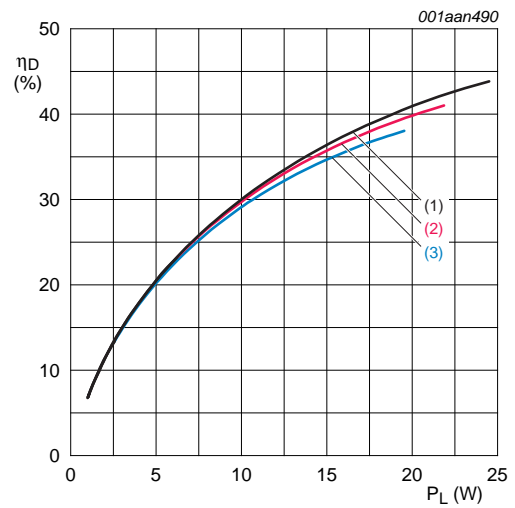
7.4 2-carrier W-CDMA

All testing performed in Class-AB production test circuit; test signal 3GPP; test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF per carrier; carrier spacing 5 MHz; $f_1 = 2500$ MHz; $f_2 = 2600$ MHz; $f_3 = 2700$ MHz; $T_{case} = 25$ °C; unless otherwise specified.



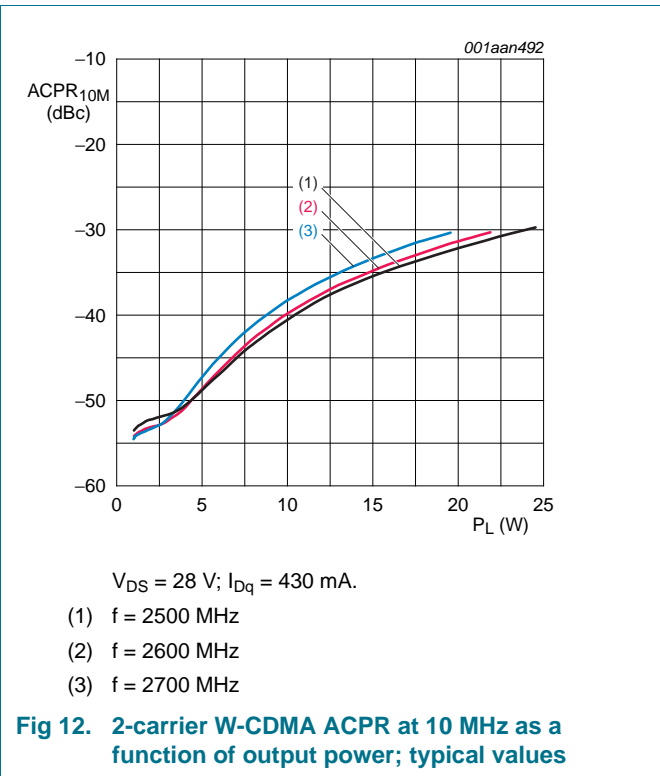
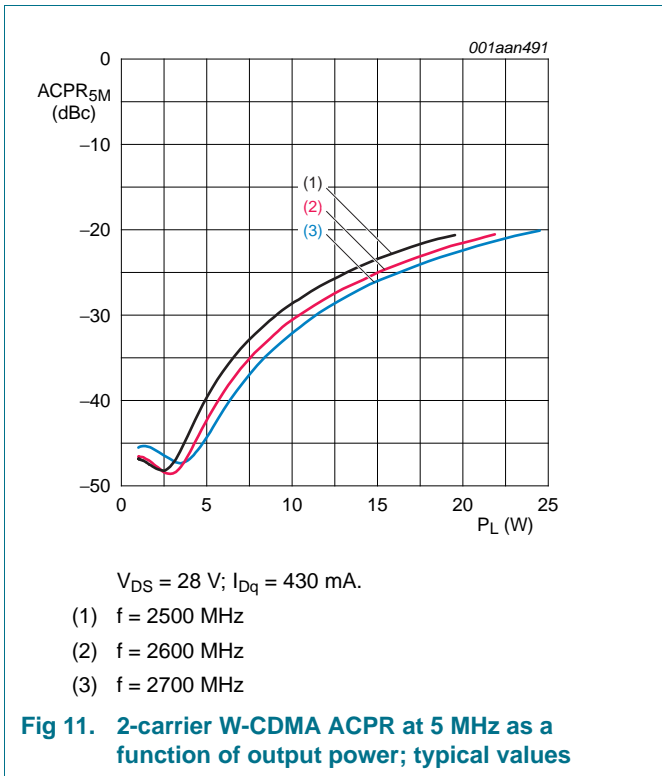
$V_{DS} = 28$ V; $I_{Dq} = 430$ mA.
 (1) $f = 2500$ MHz
 (2) $f = 2600$ MHz
 (3) $f = 2700$ MHz

Fig 9. 2-carrier W-CDMA power gain as a function of output power; typical values



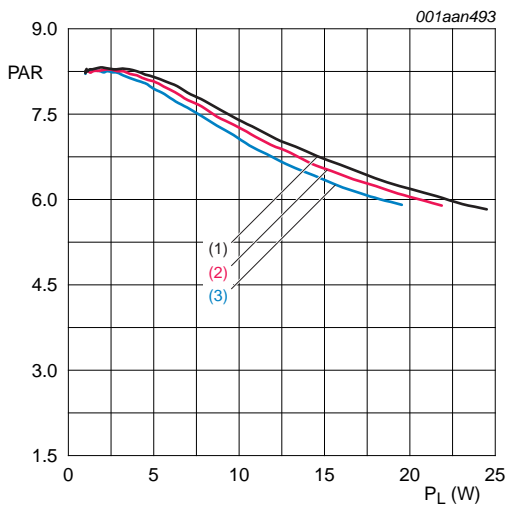
$V_{DS} = 28$ V; $I_{Dq} = 430$ mA.
 (1) $f = 2500$ MHz
 (2) $f = 2600$ MHz
 (3) $f = 2700$ MHz

Fig 10. 2-carrier W-CDMA drain efficiency as a function of output power; typical values



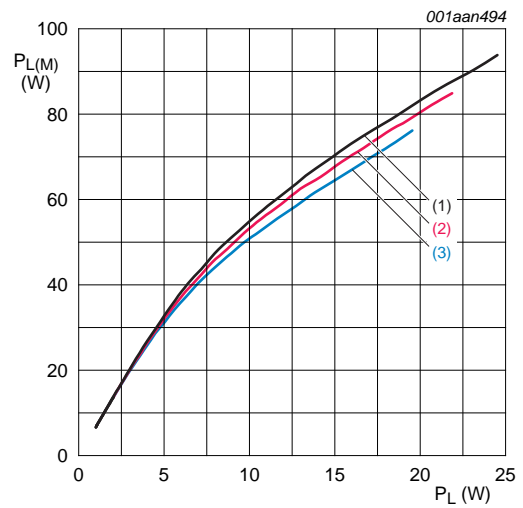
7.5 Single carrier W-CDMA

All testing performed in Class-AB production test circuit; test signal 3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF per carrier; f = 2700 MHz; T_{case} = 25 °C; unless otherwise specified.



V_{DS} = 28 V; I_{Dq} = 430 mA.
 (1) f = 2500 MHz
 (2) f = 2600 MHz
 (3) f = 2700 MHz

Fig 13. Single carrier W-CDMA peak-to-average power ratio as a function of output power; typical values



V_{DS} = 28 V; I_{Dq} = 430 mA.
 (1) f = 2500 MHz
 (2) f = 2600 MHz
 (3) f = 2700 MHz

Fig 14. Single carrier W-CDMA peak output power as a function of output power; typical values

8. Package outline

Flanged ceramic package; 2 mounting holes; 6 leads

SOT1112A

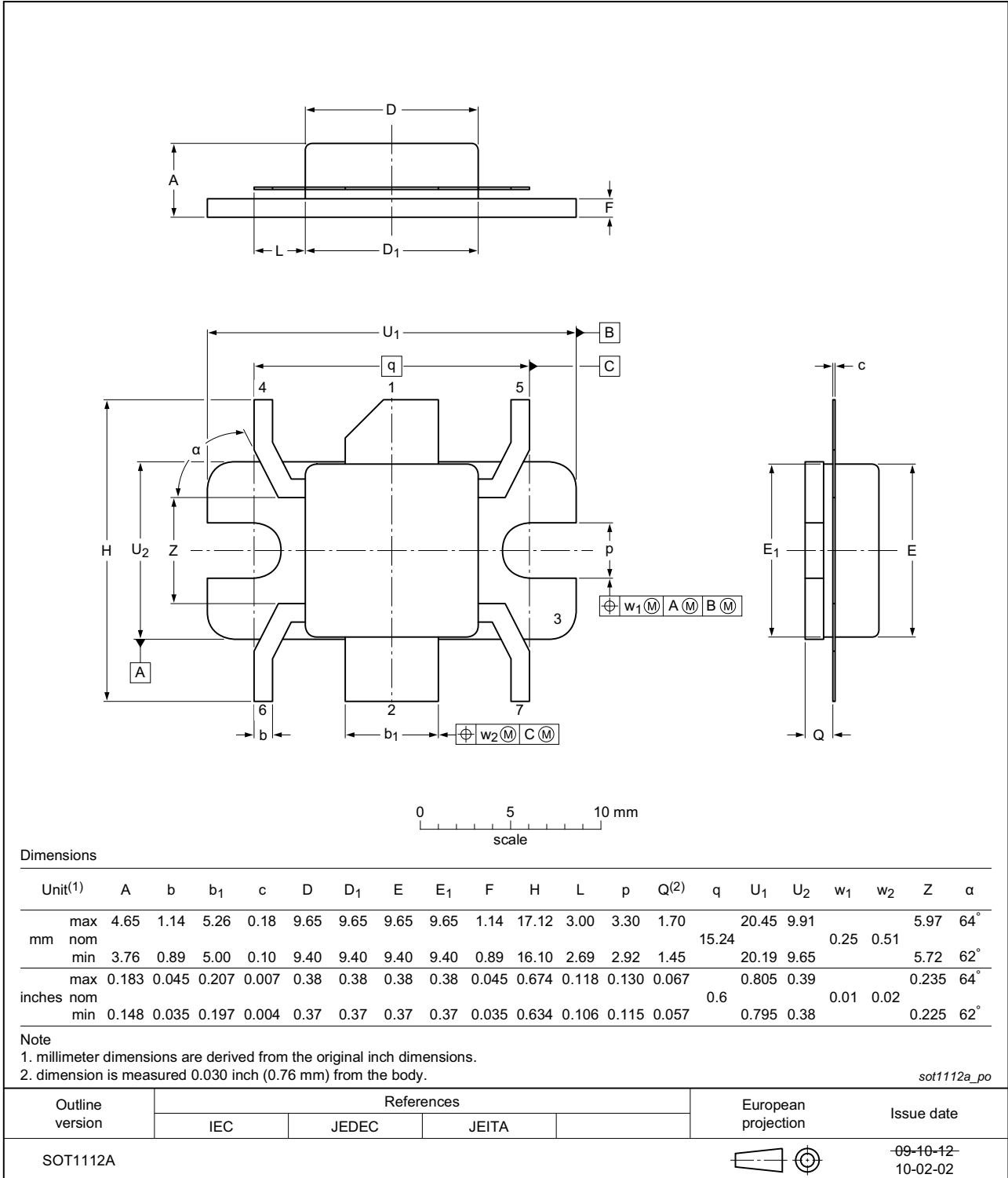


Fig 15. Package outline SOT1112A

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
IS-95	Interim Standard 95
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
PAR	Peak-to-Average Ratio
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF6G27L-50BN v.3	20141008	Product data sheet	-	BLF6G27L-50BN_6G27LS-50BN v.2
Modifications:	<ul style="list-style-type: none"> The document now describes only the eared version of this product: BLF6G27L-50BN 			
BLF6G27L-50BN_6G27LS-50BN v.2	20110407	Product data sheet	-	BLF6G27L-50BN_6G27LS-50BN v.1
BLF6G27L-50BN_6G27LS-50BN v.1	20100916	Objective data sheet	-	-

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Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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